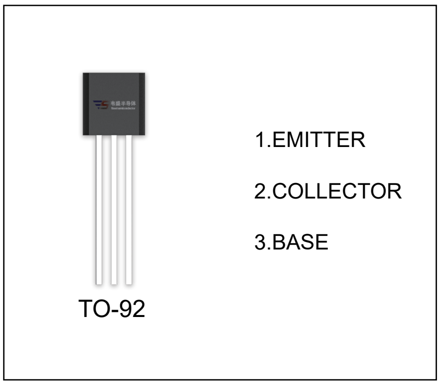
D965V TRANSISTOR (NPN)



FEATURES

- General Purpose Switching and Amplification.

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
D965V	TO-92	Bulk	1000pcs/Bag
D965V-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	22	V
V_{CEO}	Collector-Emitter Voltage	15	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	5	A
P_C	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	166	℃ /W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 1mA,I_E=0	22			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	15			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=20V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=2V, I_C=0.15mA	150			
	$h_{FE(2)}$	V_{CE}=2V, I_C=500mA	1200		2000	
	$h_{FE(3)}$	V_{CE}=2V, I_C=2A	150			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=3A,I_B=100mA			0.35	V
Transition frequency	f_T	V_{CE}=6V,I_C=50mA,f=30MHz	150			MHz